

Product Summary

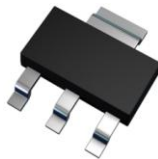
- Continuous Drain Source Voltage 60V
- On-State Resistance 100mΩ
- Nominal Load Current ($V_{IN} = 5V$) 2.8A
- Clamping Energy 490mJ

Description and Applications

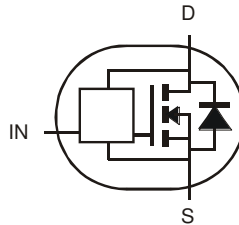
The ZXMS6006DGQ is a self protected low side IntelliFET™ MOSFET with logic level input. It integrates over-temperature, over-current, over-voltage (active clamp) and ESD protected logic level functionality. The ZXMS6006DGQ is ideal as a general purpose switch driven from 3.3V or 5V microcontrollers in harsh environments where standard MOSFETs are not rugged enough.

- Lamp Driver
- Motor Driver
- Relay Driver
- Solenoid Driver

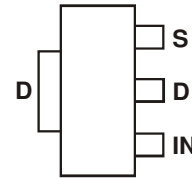
SOT223 (Type DN)



Top View



Device Symbol



Top View
Pin Out

Features and Benefits

- Compact High Power Dissipation Package
- Low Input Current
- Logic Level Input (3.3V and 5V)
- Short Circuit Protection with Auto Restart
- Over Voltage Protection (Active Clamp)
- Thermal Shutdown with Auto Restart
- Over-Current Protection
- Input Protection (ESD)
- High Continuous Current Rating
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

Mechanical Data

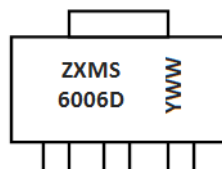
- Case: SOT223 (Type DN)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish (e3)
- Weight: 0.112 grams (Approximate)

Ordering Information (Note 5)

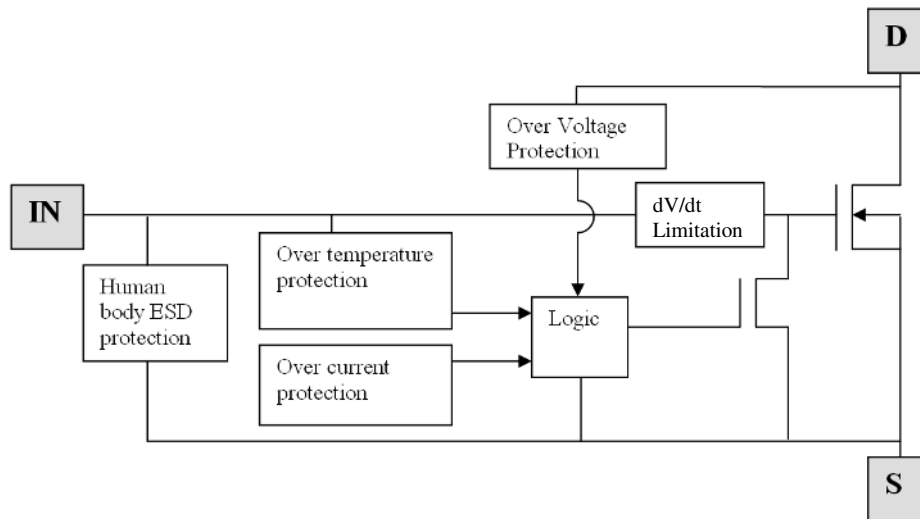
Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
ZXMS6006DGQTA	ZXMS6006D	7	12	1,000 Units

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Please refer to <https://www.diodes.com/quality/>.
 5. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



ZXMS6006D = Product Type Marking Code
 YWW = Date Code Marking
 Y or \bar{Y} = Last Digit of Year (ex: 8 = 2018)
 WW or $\bar{W}W$ = Week Code (01 to 53)

Functional Block Diagram

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Continuous Drain-Source Voltage	V_{DS}	60	V
Drain-Source Voltage for Short Circuit Protection	$V_{DS(SC)}$	16	V
Continuous Input Voltage	V_{IN}	-0.5 to +6.0	V
Continuous Input Current @ $-0.2\text{V} \leq V_{IN} \leq 6\text{V}$	I_{IN}	No limit $ I_{IN} \leq 2$	mA
Continuous Input Current @ $V_{IN} < -0.2\text{V}$ or $V_{IN} > 6\text{V}$			
Pulsed Drain Current @ $V_{IN} = 3.3\text{V}$	I_{DM}	11	A
Pulsed Drain Current @ $V_{IN} = 5\text{V}$	I_{DM}	13	A
Continuous Source Current (Body Diode) (Note 6)	I_S	2	A
Pulsed Source Current (Body Diode)	I_{SM}	12	A
Unclamped Single Pulse Inductive Energy, $T_J = +25^\circ\text{C}$, $I_D = 0.5\text{A}$, $V_{DD} = 24\text{V}$	E_{AS}	490	mJ
Electrostatic Discharge (Human Body Model)	V_{ESD}	4000	V
Charged Device Model	V_{CDM}	1000	V

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at $T_A = +25^\circ\text{C}$ (Note 6)	P_D	1.3	W
Linear Derating Factor		10.4	mW/ $^\circ\text{C}$
Power Dissipation at $T_A = +25^\circ\text{C}$ (Note 7)	P_D	3.0	W
Linear Derating Factor		24	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	96	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Ambient (Note 7)	$R_{\theta JA}$	42	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case (Note 8)	$R_{\theta JC}$	12	$^\circ\text{C}/\text{W}$
Operating Temperature Range	T_J	-40 to +150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150	$^\circ\text{C}$

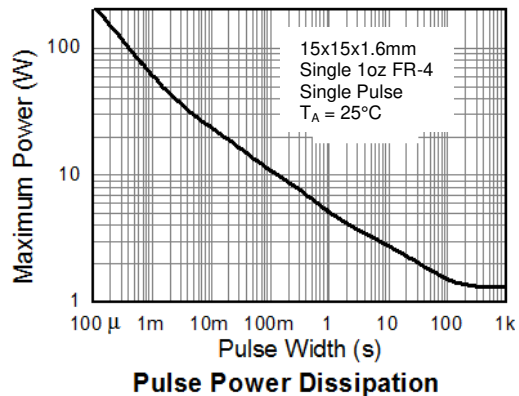
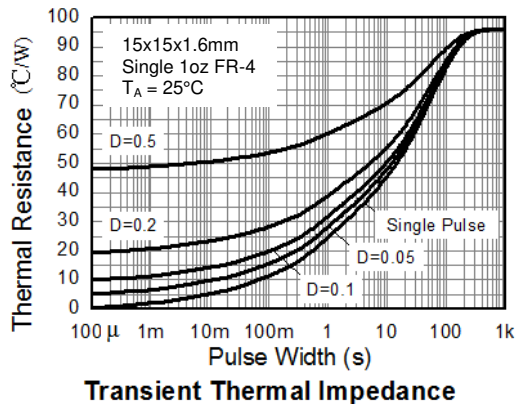
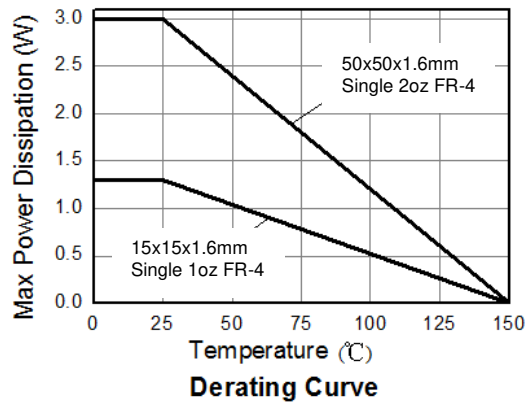
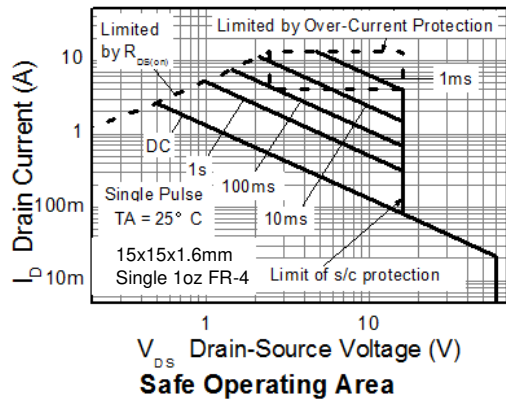
Notes: 6. For a device surface mounted on 15mm x 15mm single sided 1oz weight copper on 1.6mm FR-4 board, in still air conditions.
7. For a device surface mounted on 50mm x 50mm single sided 2oz weight copper on 1.6mm FR-4 board, in still air conditions.
8. Thermal resistance between junction and the mounting surfaces of drain and source pins.

Recommended Operating Conditions

The ZXMS6006DGQ is optimized for use with μ C operating from 3.3V and 5V supplies.

Characteristic	Symbol	Min	Max	Unit
Input Voltage Range	V_{IN}	0	5.5	V
Ambient Temperature Range	T_A	-40	+125	$^{\circ}$ C
High Level Input Voltage for MOSFET to be on	V_{IH}	3	5.5	V
Low level input voltage for MOSFET to be off	V_{IL}	0	0.7	V
Peripheral Supply Voltage (voltage to which load is referred)	V_P	0	16	V

Thermal Characteristics



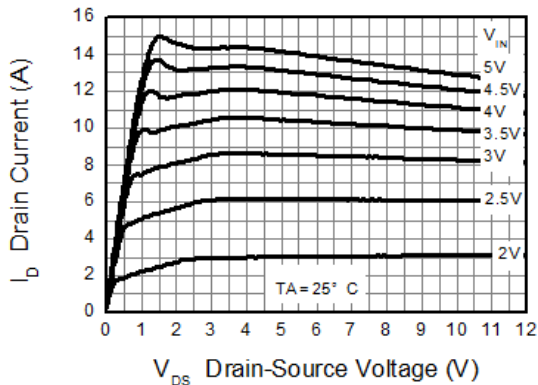
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Static Characteristics						
Drain-Source Clamp Voltage	V _{DS(AZ)}	60	65	70	V	I _D = 10mA
Off State Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 12V, V _{IN} = 0V
		—	—	2		V _{DS} = 36V, V _{IN} = 0V
Input Threshold Voltage	V _{IN(TH)}	0.7	1.15	1.5	V	V _{DS} = V _{GS} , I _D = 1mA
Input Current	I _{IN}	—	60	100	μA	V _{IN} = 3V
		—	120	200		V _{IN} = 5V
Input Current While Over Temperature Active	—	—	—	400	μA	V _{IN} = 5V
Static Drain-Source On-State Resistance	R _{DS(ON)}	—	85	125	mΩ	V _{IN} = 3V, I _D = 1A
		—	75	100		V _{IN} = 5V, I _D = 1A
Continuous Drain Current (Note 6)	I _D	2.0	—	—	A	V _{IN} = 3V, T _A = +25°C
		2.2	—	—		V _{IN} = 5V, T _A = +25°C
Continuous Drain Current (Note 7)		2.6	—	—		V _{IN} = 3V, T _A = +25°C
		2.8	—	—		V _{IN} = 5V, T _A = +25°C
Current Limit (Note 9)	I _{D(LIM)}	4	8	—	A	V _{IN} = 3V
		6	13	—		V _{IN} = 5V
Dynamic Characteristics						
Turn On Delay Time	t _{D(ON)}	—	8.6	—	μs	V _{DD} = 12V, I _D = 1A, V _{GS} = 5V
Rise Time	t _R	—	18	—		
Turn Off Delay Time	t _{D(OFF)}	—	34	—		
Fall Time	t _F	—	15	—		
Over-Temperature Protection						
Thermal Overload Trip Temperature (Note 10)	T _{JT}	+150	+175	—	°C	—
Thermal Hysteresis (Note 10)	f _t	—	+10	—	°C	—

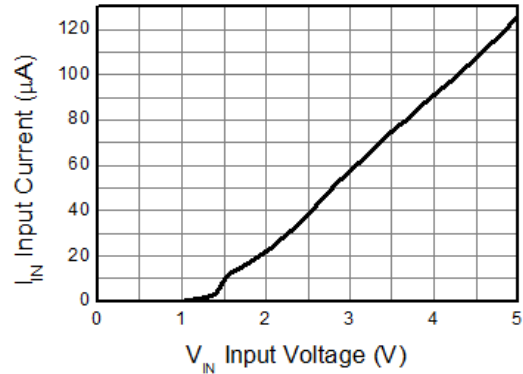
Notes: 9. The drain current is restricted only when the device is in saturation (see graph 'Typical Output Characteristic'). This allows the device to be used in the fully on state without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside saturation makes current limit unnecessary.

10. Over-temperature protection is designed to prevent device destruction under fault conditions. Fault conditions are considered as "outside" normal operating range, so this part is not designed to withstand over-temperature for extended periods..

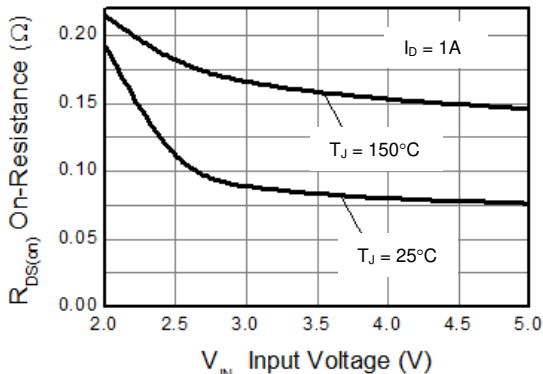
Typical Characteristics



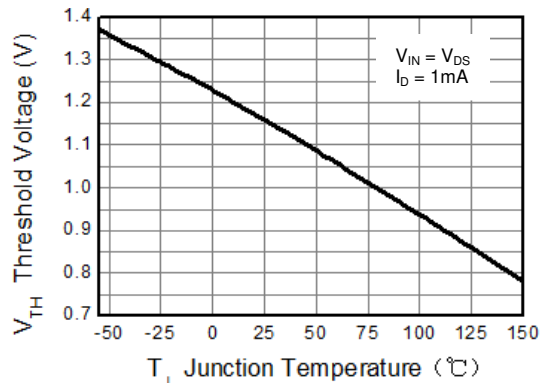
Typical Output Characteristic



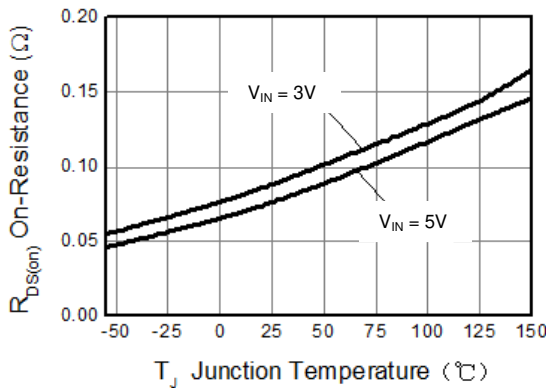
Input Current vs Input Voltage



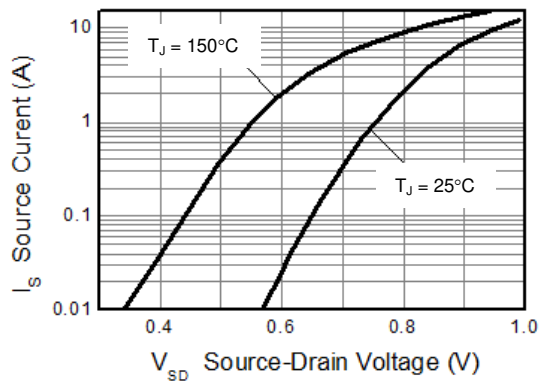
On-Resistance vs Input Voltage



Threshold Voltage vs Temperature

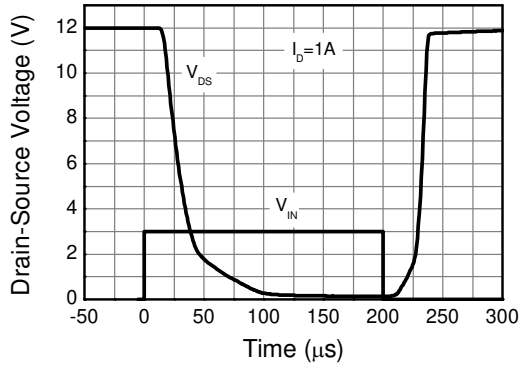


On-Resistance vs Temperature

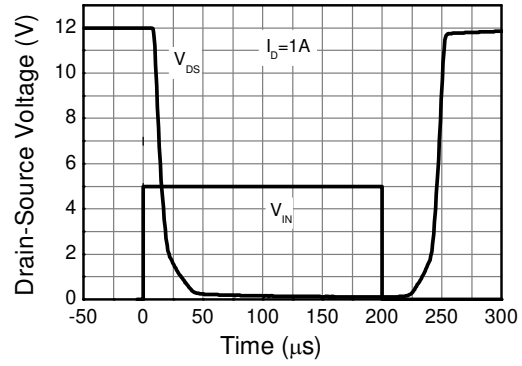


Reverse Diode Characteristic

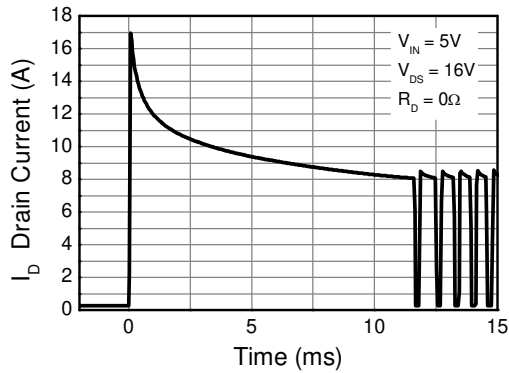
Typical Characteristics (Cont.)



Switching Speed



Switching Speed

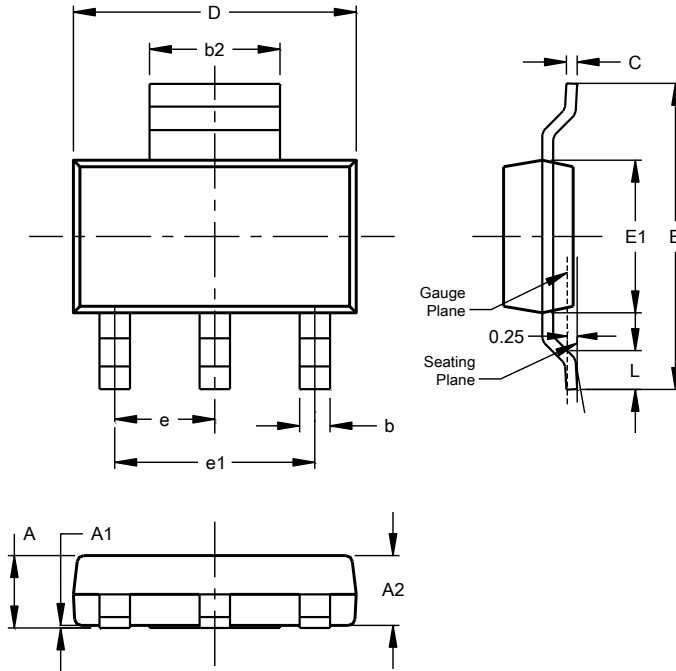


Typical Short Circuit Protection

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223 (Type DN)

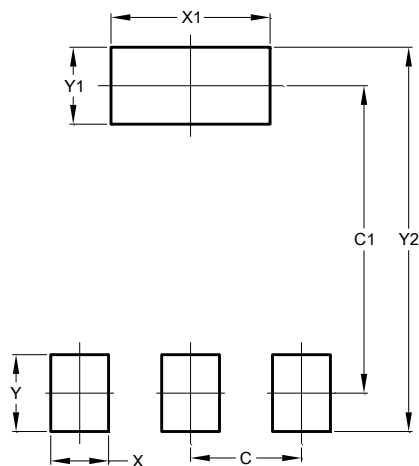


SOT223 (Type DN)			
Dim	Min	Max	Typ
A	--	1.70	--
A1	0.01	0.15	--
A2	1.50	1.68	1.60
b	0.60	0.80	0.70
b2	2.90	3.10	--
c	0.20	0.32	--
D	6.30	6.70	--
E	6.70	7.30	--
E1	3.30	3.70	--
e	--	--	2.30
e1	--	--	4.60
L	0.85	--	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223 (Type DN)



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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